



Technical Data Sheet

5mm Infrared LED , T-1

IR333C

Features

- High reliability
- High radiant intensity
- Peak wavelength $\lambda_p=940\text{nm}$
- 2.54mm Lead spacing
- Low forward voltage
- Pb Free
- This product itself will remain within RoHS compliant version.



Descriptions

- EVERLIGHT's Infrared Emitting Diode (IR333C) is a high intensity diode , molded in a water clear plastic package.
- The device is spectrally matched with phototransistor , photodiode and infrared receiver module.

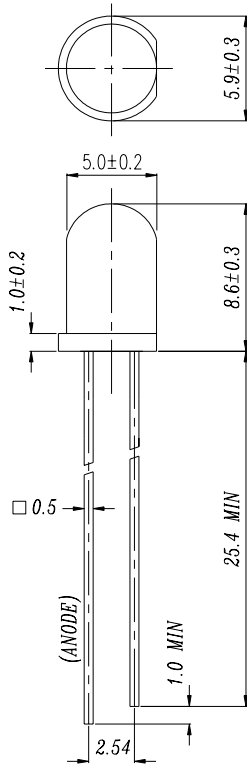
Applications

- Free air transmission system
- Infrared remote control units with high power requirement
- Smoke detector
- Infrared applied system

Device Selection Guide

LED Part No.	Chip	Lens Color
	Material	
IR333C	GaAlAs	Water clear

Package Dimensions



- Notes:** 1.All dimensions are in millimeters
 2.Tolerances unless dimensions ±0.25mm

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Units
Continuous Forward Current	I _F	100	mA
Peak Forward Current	I _{FP}	1.0	A
Reverse Voltage	V _R	5	V
Operating Temperature	T _{opr}	-40 ~ +85	°C
Storage Temperature	T _{stg}	-40 ~ +85	°C
Soldering Temperature	T _{sol}	260	°C
Power Dissipation at(or below) 25°C Free Air Temperature	P _d	150	mW

Notes: *1:I_{FP} Conditions--Pulse Width ≤ 100 μs and Duty ≤ 1%.

*2:Soldering time ≤ 5 seconds.

Electro-Optical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Radiant Intensity	Ee	I _F =20mA	7.8	15	--	mW/sr
		I _F =100mA Pulse Width ≤ 100 μs ,Duty ≤ 1%	--	60	--	
		I _F =1A Pulse Width ≤ 100 μs ,Duty ≤ 1%	--	450	--	
Peak Wavelength	λ _p	I _F =20mA	--	940	--	nm
Spectral Bandwidth	Δλ	I _F =20mA	--	45	--	nm
Forward Voltage	V _F	I _F =20mA		1.2	1.5	V
		I _F =100mA Pulse Width ≤ 100 μs ,Duty ≤ 1%	--	1.4	1.85	
Reverse Current	I _R	V _R =5V	--	--	10	μA
View Angle	2θ _{1/2}	I _F =20mA	--	20	--	deg

Rank

 Condition : I_F=20mA

Unit : mW/sr

Bin Number	M	N	P	Q
Min	7.8	11.0	15.0	21.0
Max	12.5	17.6	24.0	34.0

Typical Electro-Optical Characteristics Curves

Fig.1 Forward Current vs. Ambient Temperature

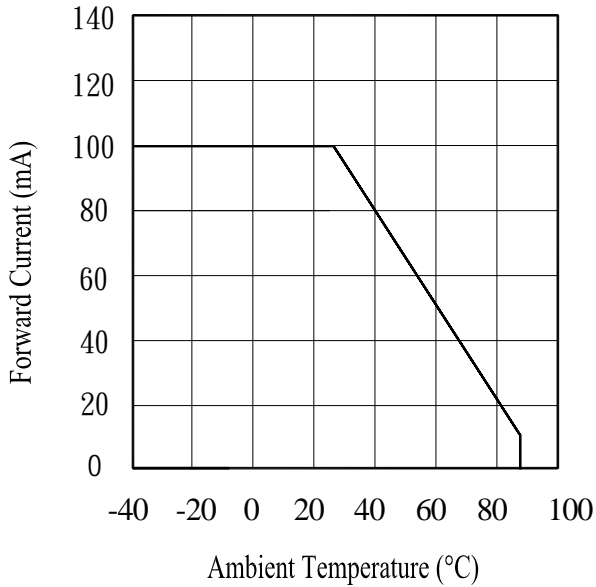


Fig.2 Spectral Distribution

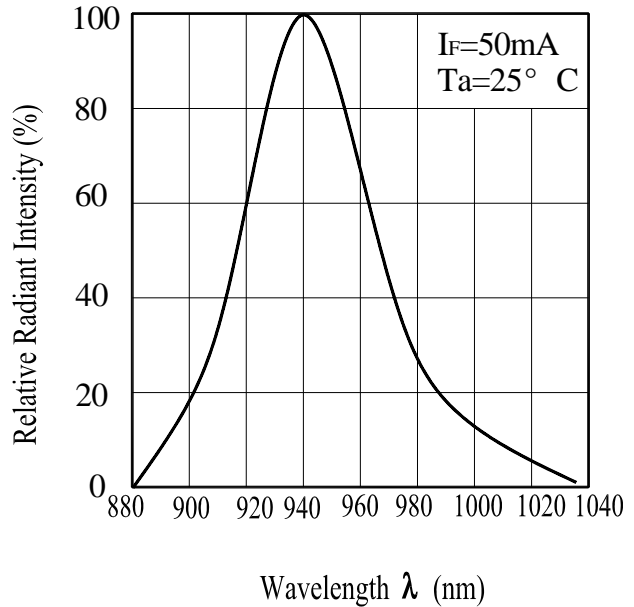


Fig.3 Peak Emission Wavelength vs. Ambient Temperature

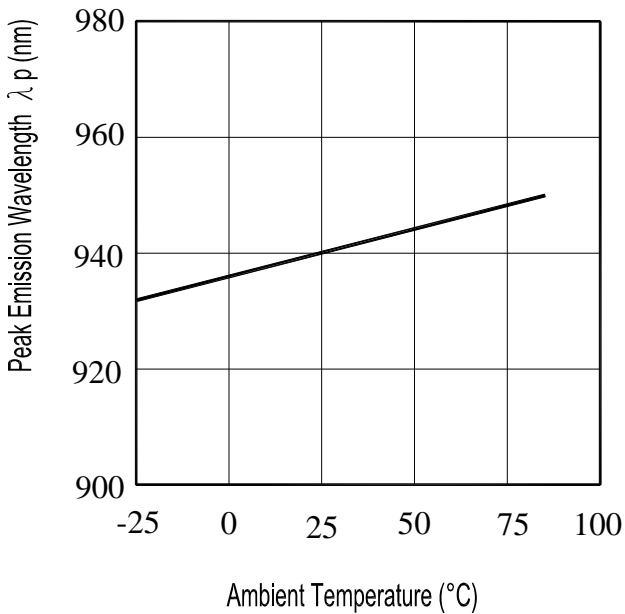
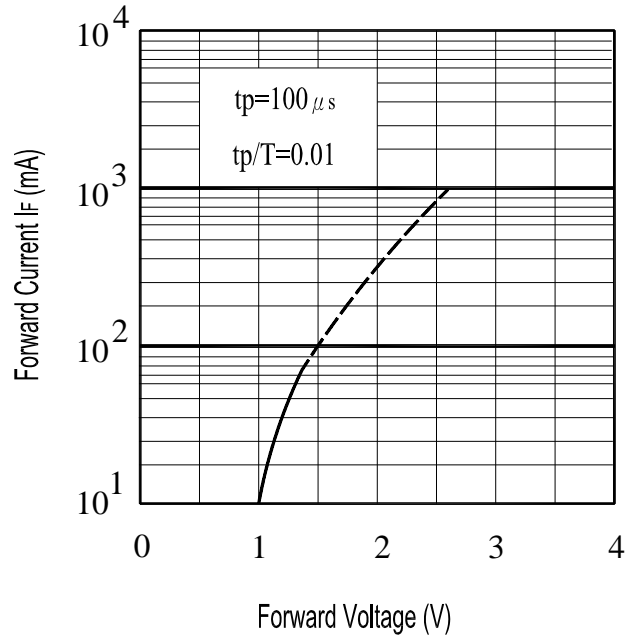


Fig.4 Forward Current vs. Forward Voltage



Typical Electro-Optical Characteristics Curves

Fig.5 Relative Intensity vs.

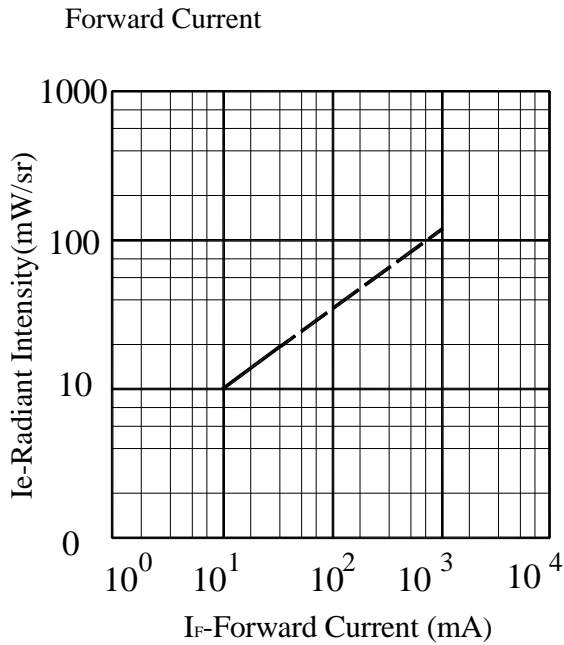


Fig.6 Relative Radiant Intensity vs.

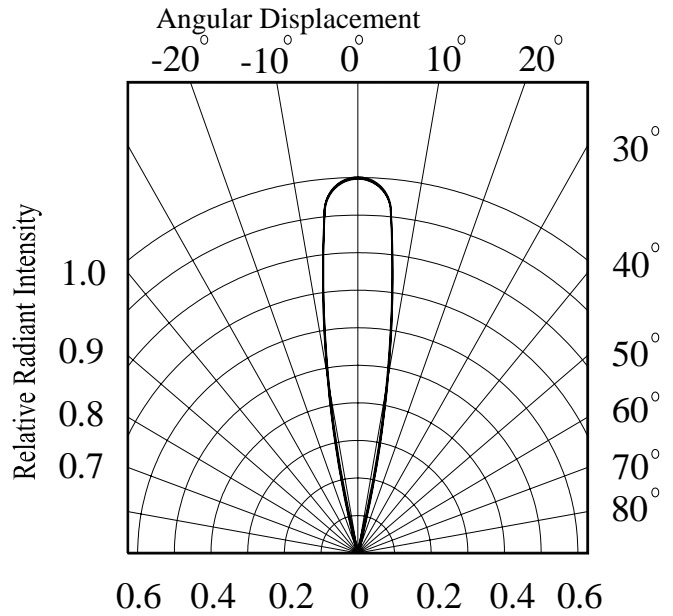


Fig.7 Relative Intensity vs.

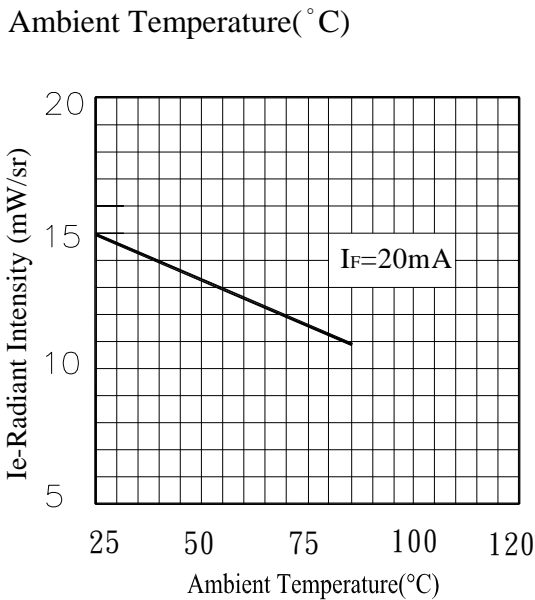
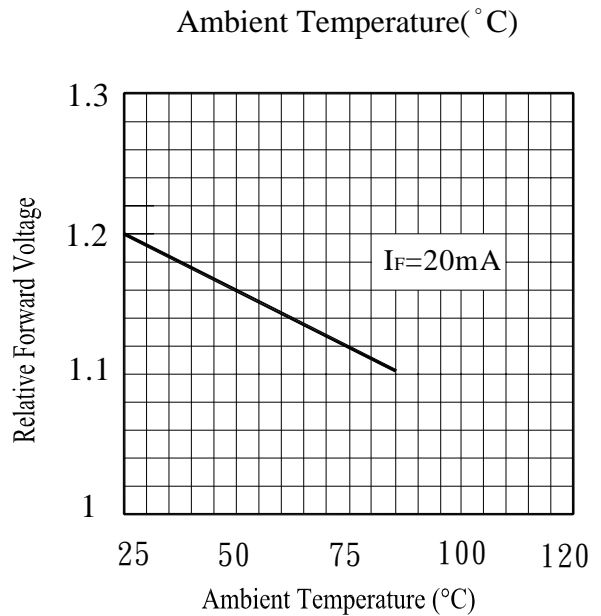


Fig.8 Forward Current vs.





Technical Data Sheet

5mm Phototransistor T-1

PT333-3B

Features

- Fast response time
- High photo sensitivity
- Pb free
- This product itself will remain within RoHS compliant version.

Descriptions

- PT333-3B is a high speed and high sensitive NPN silicon NPN epitaxial planar phototransistor molded in a standard 5 mm package. Due to its black epoxy the device is sensitive to visible and near Infrared radiation.



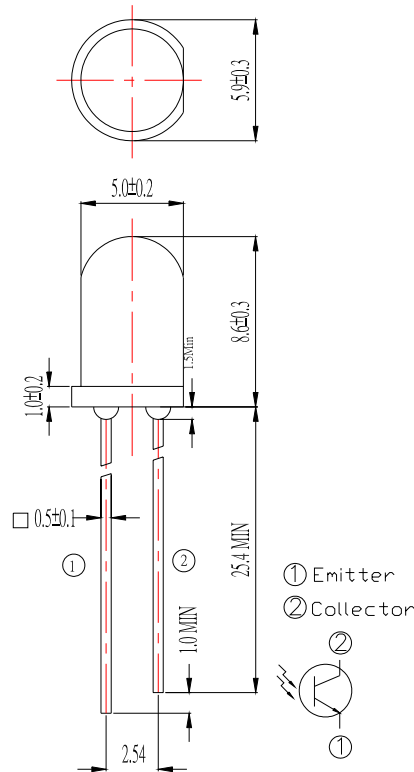
Applications

- Infrared applied system
- Camera
- Cockroach catcher

Device Selection Guide

LED Part No.	Chip	Lens Color
	Material	
PT333-3B	Silicon	Black

Package Dimensions



- Notes:** 1.All dimensions are in millimeters
 2.Tolerances unless dimensions $\pm 0.25\text{mm}$

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Collector-Voltage	V_{ECO}	5	V
Collector Current	I_C	20	mA
Operating Temperature	T_{opr}	-25 ~ +85°C	°C
Storage Temperature	T_{stg}	-40 ~ +85°C	°C
Lead Soldering Temperature(*1)	T_{sol}	260	°C
Power Dissipation at (or below) 25°C Free Air Temperature	P_c	75	mW

Notes: *1:Soldering time ≤ 5 seconds.

Electro-Optical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Collector – Emitter Breakdown Voltage	BV_{CEO}	$I_C=100\ \mu A$ $E_e=0mW/cm^2$	30	---	---	V
Emitter-Collector Breakdown Voltage	BV_{ECO}	$I_E=100\ \mu A$ $E_e=0mW/cm^2$	5	---	---	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2mA$ $E_e=1mW/cm^2$	---	---	0.4	V
Rise Time	t_r	$V_{CE}=5V$ $I_C=1mA$	---	15	---	μS
Fall Time	t_f	$RL=1000\ \Omega$	---	15	---	
Collector Dark Current	I_{CEO}	$E_e=0mW/cm^2$ $V_{CE}=20V$	---	---	100	nA
On State Collector Current	$I_{C(on)}$	$E_e=1mW/cm^2$ $V_{CE}=5V$	0.7	3.0	---	mA
Wavelength of Peak Sensitivity	λ_p	---	---	940	---	nm
Rang of Spectral Bandwidth	$\lambda_{0.5}$	---	---	840-1100	---	nm

Rankings

Parameter	Symbol	Min	Max	Unit	Test Condition
G	$I_{C(ON)}$	0.70	1.90	mA	$V_{CE}=5V$ $E_e=1mW/cm^2$
H		1.14	2.60		
J		1.77	3.61		
K		2.67	5.07		
L		4.18	7.07		

Typical Electro-Optical Characteristics Curves

Fig.1 Collector Power Dissipation vs. Ambient Temperature

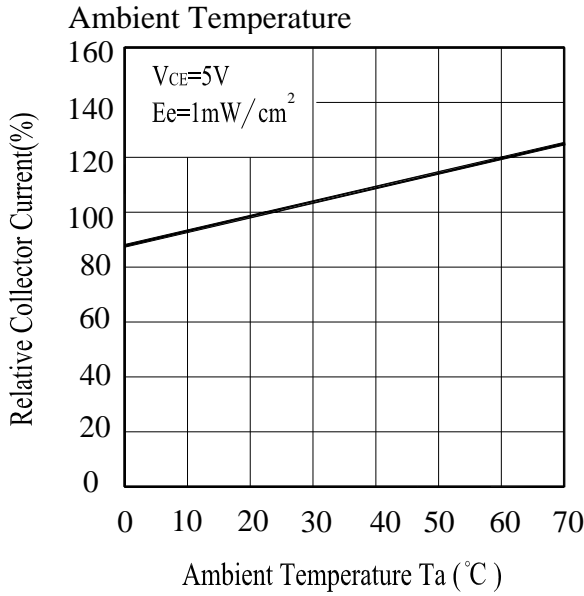


Fig.2 Spectral Sensitivity

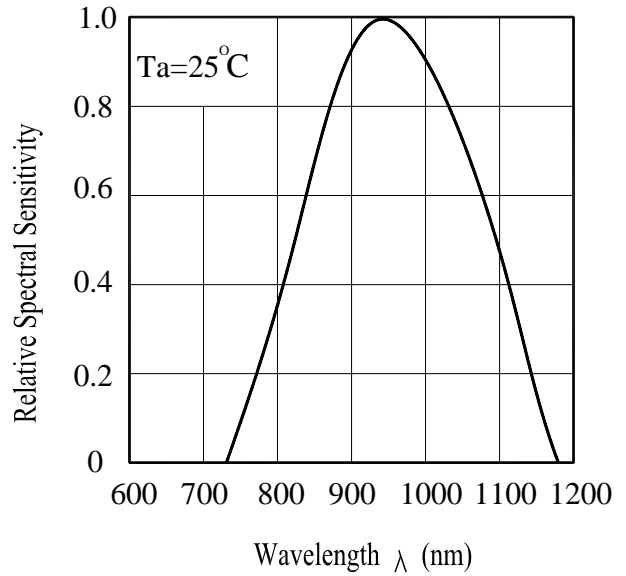


Fig.3 Relative Collector Current vs. Ambient Temperature

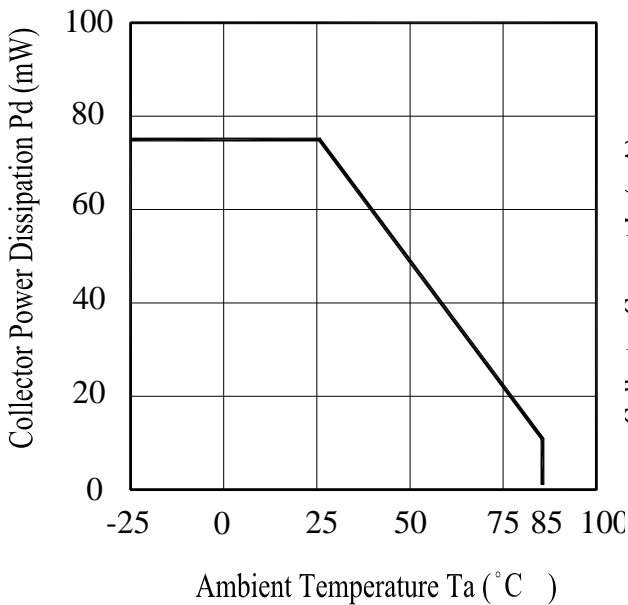
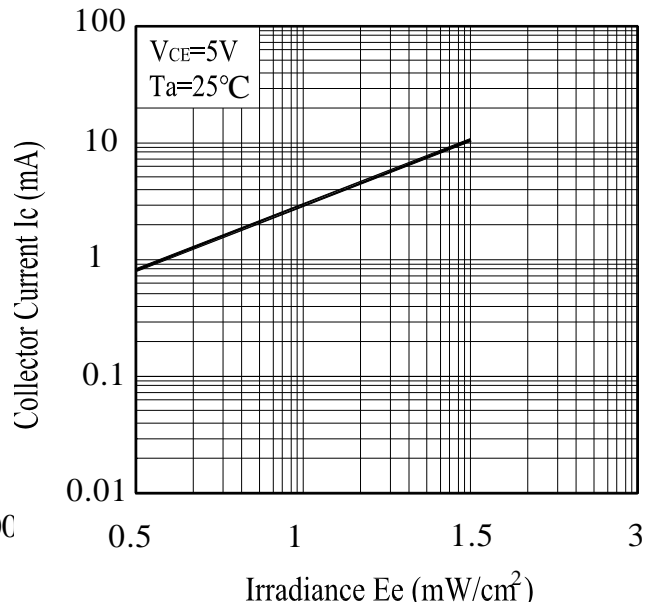


Fig.4 Collector Current vs. Irradiance



Typical Electro-Optical Characteristics Curves

Fig.5 Collector Dark Current vs. Ambient Temperature

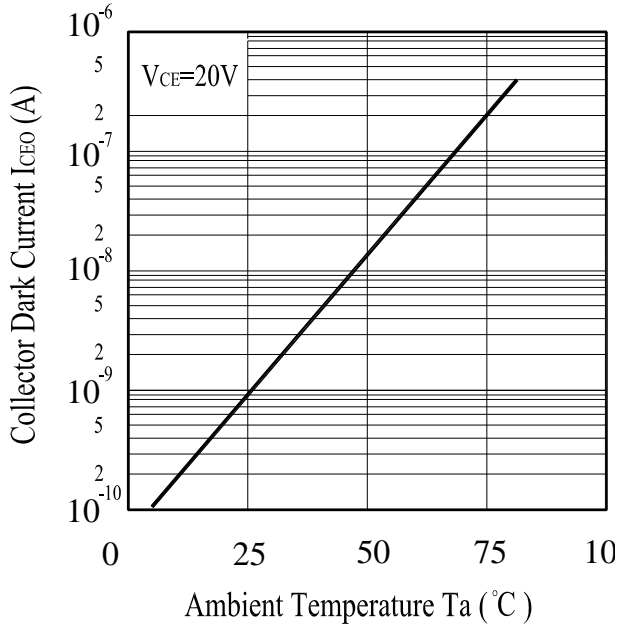
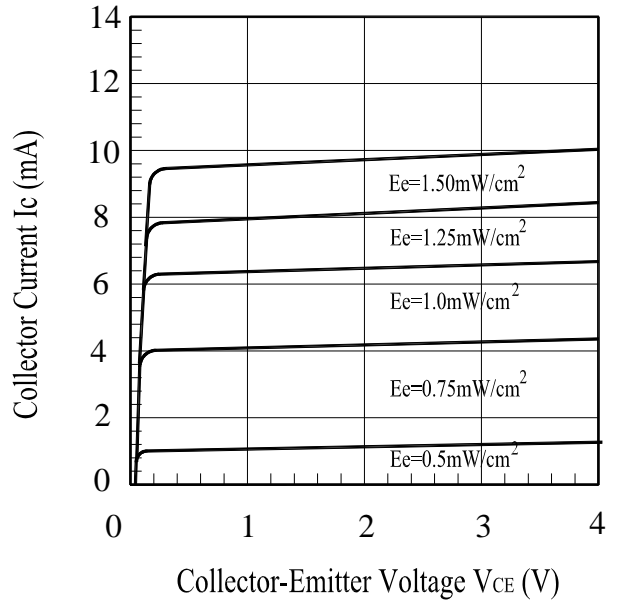


Fig.6 Collector Current vs. Collector-Emitter Voltage



Reliability Test Item And Condition

The reliability of products shall be satisfied with items listed below.

Confidence level : 90%

LTPD : 10%

NO.	Item	Test Conditions	Test Hours/ Cycles	Sample Sizes	Failure Judgement Criteria	Ac/Re
1	Solder Heat	TEMP. : 260°C±5°C	10secs	22pcs	$I_{C(ON)} \leq L \times 0.8$ L : the initial test value	0/1
2	Temperature Cycle	H : +100°C 15mins ↑ 5mins ↓ L : -40°C 15mins	300Cycles	22pcs		0/1
3	Thermal Shock	H : +100°C 5mins ↑ 10secs ↓ L : -10°C 5mins	300Cycles	22pcs		0/1
4	High Temperature Storage	TEMP. : +100°C	1000hrs	22pcs		0/1
5	Low Temperature Storage	TEMP. : -40°C	1000hrs	22pcs		0/1
6	DC Operating Life	$V_{CE}=5V$	1000hrs	22pcs		0/1
7	High Temperature/ High Humidity	85°C / 85% R.H	1000hrs	22pcs		0/1



Packing Quantity Specification

1.500PCS/1Bag , 5Bags/1Box

2.10Boxes/1Carton

Label Form Specification



CPN:

CPN: Customer's Production Number

P/N:

P/N : Production Number



QTY: Packing Quantity

PT333-3B

CAT: Ranks

QTY:

CAT:

HUE: Peak Wavelength



HUE:

REF: Reference

LOT NO:

REF:

LOT No: Lot Number



Notes

1. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification.
2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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